

Figure S1: (a) Output characteristics ($I_{DS} \times V_{DS}$) of the transistor with untreated cr-PVA layer. Open symbols correspond to leakage current (I_{GS}), whereas solid symbols represent channel current (I_{DS}); (b) transfer characteristics of the same device.

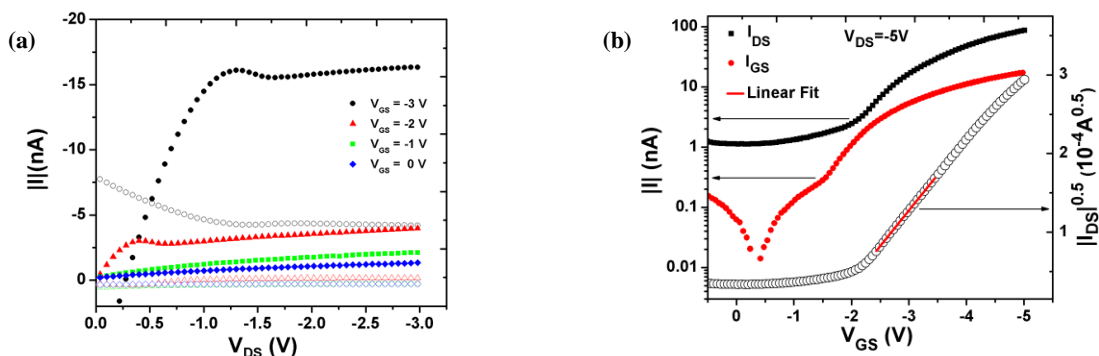


Figure S2: (a) Output characteristics ($I_{DS} \times V_{DS}$) of the transistor in which the cr-PVA layer was treated with 0.3 mg/mL of CTAB solution. Open symbols correspond to leakage current (I_{GS}), whereas solid symbols represent channel current (I_{DS}); (b) transfer characteristics of the same device.

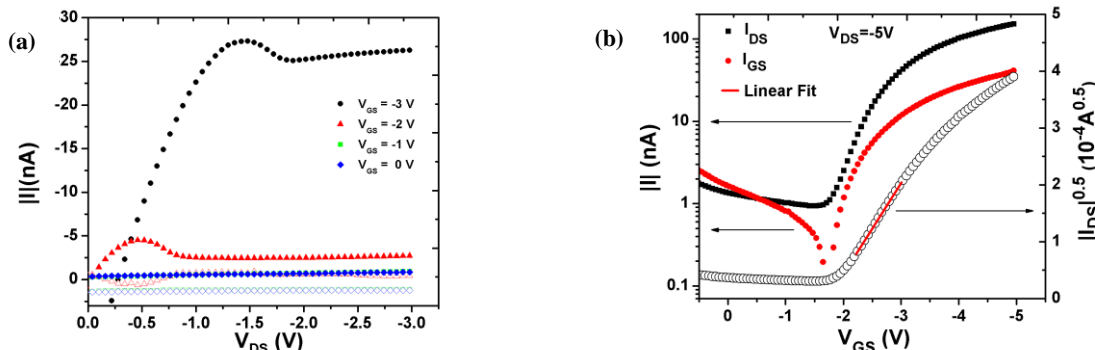


Figure S3: (a) Output characteristics ($I_{DS} \times V_{DS}$) of the transistor in which the cr-PVA layer was treated with 0.5 mg/mL of CTAB solution. Open symbols correspond to leakage current (I_{GS}), whereas solid symbols represent channel current (I_{DS}); (b) transfer characteristics of the same device.

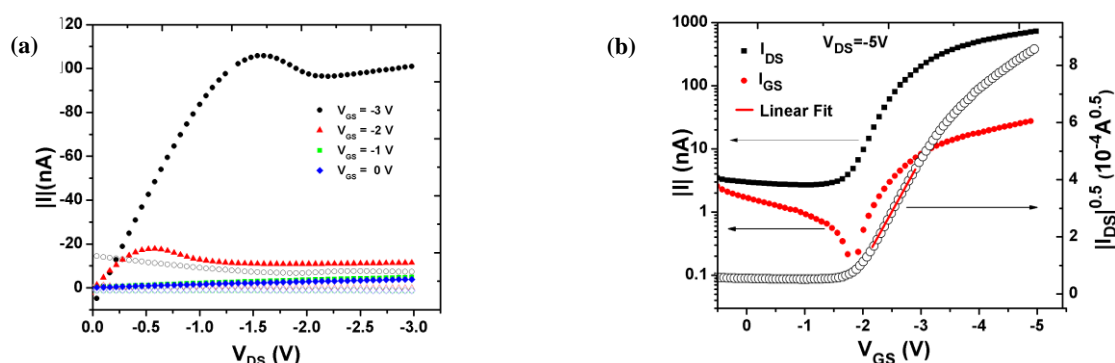


Figure S4: (a) Output characteristics ($I_{DS} \times V_{DS}$) of the transistor in which the cr-PVA layer was treated with 3.0 mg/mL of CTAB solution. Open symbols correspond to leakage current (I_{GS}), whereas solid symbols represent channel current (I_{DS}); (b) transfer characteristics of the same device.